Docket No.: 21302/0203830-US0

(PATENT)

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Euijoon Yoon et al.

Application No.: 10/563,854

Confirmation No.: 3828

Filed: June 9, 2006

Art Unit: 2823

For: GROWTH METHOD FOR NITRIDE

SEMICONDUCTOR EPITAXIAL LAYERS

Examiner: Maldonado, Julio J.

## **AMENDMENT IN RESPONSE TO NON-FINAL OFFICE ACTION**

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450 August 4, 2009

Dear Sir:

## **INTRODUCTORY COMMENTS**

In response to the Non-Final Office Action dated March 4, 2009, please amend the above-identified U.S. patent application as follows.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 8 of this paper.